## P-Channel 40-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

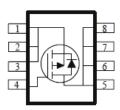
- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-40	19 @ V <sub>GS</sub> = -10V	-35 <sup>c</sup>	
-40	$27 @ V_{GS} = -4.5V$	-33	



**FREE** 





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			-40	V		
Gate-Source Voltage			±20	٧		
	T <sub>C</sub> =25°C	I <sub>D</sub>	-35 <sup>c</sup>	A		
Continuous Drain Current	T <sub>C</sub> =70°C		-31			
Continuous Diain Current	T <sub>A</sub> =25°C		-12 <sup>a</sup>			
	T <sub>A</sub> =70°C		-8.4 <sup>a</sup>			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-60				
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-4.7				
	T <sub>C</sub> =25°C		42	- W		
Power Dissipation	T <sub>C</sub> =70°C	$P_D$	27			
ir ower dissipation	T <sub>A</sub> =25°C	' D	3.5 <sup>a</sup>			
	T <sub>A</sub> =70°C		2 <sup>a</sup>			
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
IMAXIIIIUIII JUIICUOII-to-AIIIbleIIt	Steady State	IXOJA	81				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	3				

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

#### **Electrical Characteristics**

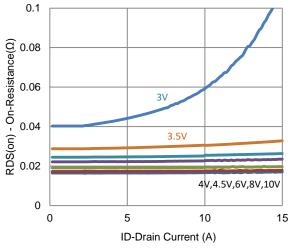
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zelo Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-18			Α	
Dunin Course On Braintana a	r	$V_{GS} = -10 \text{ V}, I_{D} = -8.9 \text{ A}$			19	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -7.2 \text{ A}$			27	11177	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -8.9 \text{ A}$		9		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -2.4 \text{ A}, V_{GS} = 0 \text{ V}$		-0.77		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V},$		23			
Gate-Source Charge	$Q_{gs}$	$I_{DS} = -20 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -8.9 \text{ A}$		5.9		nC	
Gate-Drain Charge	$Q_{gd}$	ID = -0.9 V		10			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -20 \text{ V}, R_L = 2.3 \Omega,$		5			
Rise Time	t <sub>r</sub>	$V_{DS} = -20 \text{ V}, R_L - 2.3 \Omega,$ $I_D = -8.9 \text{ A},$		42		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		84		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 22		43			
Input Capacitance	C <sub>iss</sub>			2348			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		266		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			232			

#### Notes

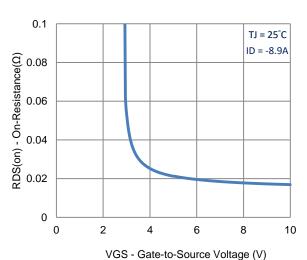
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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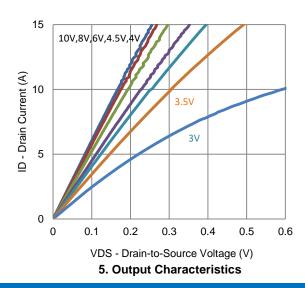
### **Typical Electrical Characteristics**

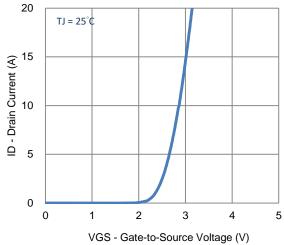


#### 1. On-Resistance vs. Drain Current

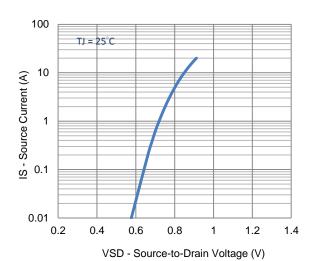


3. On-Resistance vs. Gate-to-Source Voltage

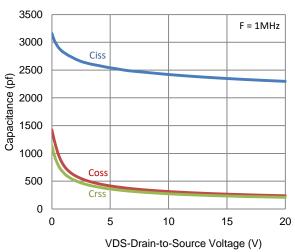




2. Transfer Characteristics

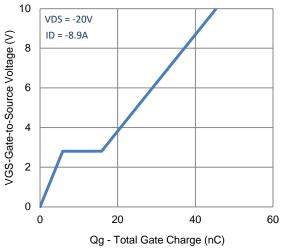


4. Drain-to-Source Forward Voltage

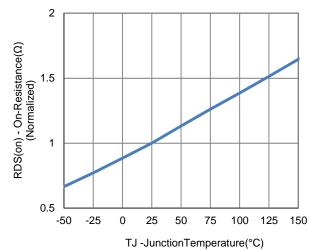


6. Capacitance

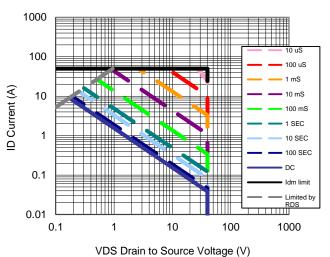
### **Typical Electrical Characteristics**



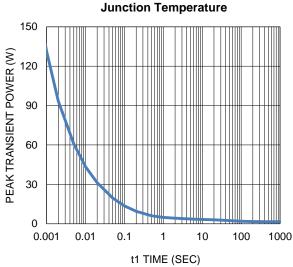




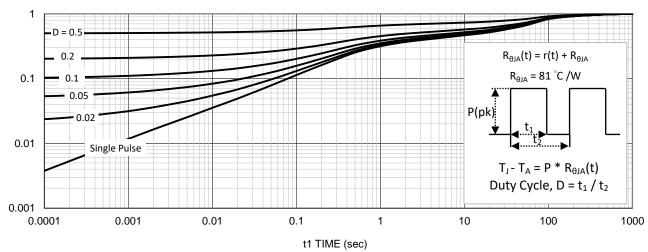
8. Normalized On-Resistance Vs



9. Safe Operating Area

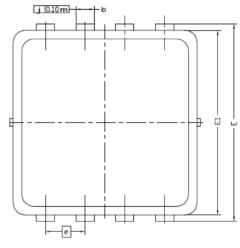


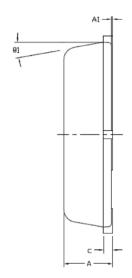
10. Single Pulse Maximum Power Dissipation

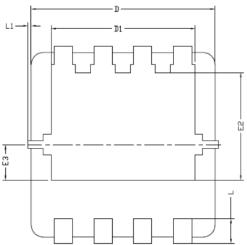


11. Normalized Thermal Transient Junction to Ambient

# Package Information







DIM.	MILLIMETERS			INCHES		
DIM	NIM	NDM	MAX	MIN	NDM	MAX
Α	0,700	0,80	0.900	0,0276	0,0315	0,0354
A1	0.00		0,05	0,000		0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2,35 BSC			0.093 BSC		
Ε	3.20 BSC			0.126 BSC		
E1	3.00 B2C			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0,575 BSC			0.023 BSC		
е	0.65 BSC			0,026 BSC		
Ĺ	0,30	0,40	0,50	0.0118	0,0157	0,0197
L1	0		0,100	0		0.004
91	0°	10°	12°	0°	10°	12°